

Sudip Ghosh

List of Publications by Year in descending order

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19
papers

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citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of Via-Inductance on Stability Behavior of Large Gate-Periphery Multi-finger RF Transistors. , 2019, , .		0
2	Simulation, Characterization and Parameter Extraction of Radiation Hardened MOSFET. , 2019, , .		2
3	ASM GaN: Industry Standard Model for GaN RF and Power Devicesâ€™ Part 1: DC, CV, and RF Model. IEEE Transactions on Electron Devices, 2019, 66, 80-86.	1.6	97
4	Physics-based Compact Modeling of MSM-2DEG GaN-based Varactors for THz Applications. , 2018, , .		3
5	Analysis and Modeling of Cross-Coupling and Substrate Capacitances in GaN HEMTs for Power-Electronic Applications. IEEE Transactions on Electron Devices, 2017, 64, 816-823.	1.6	34
6	Pole-Zero Approach to Analyze and Model the Kink in Gain-Frequency Plot of GaN HEMTs. IEEE Microwave and Wireless Components Letters, 2017, 27, 266-268.	2.0	16
7	A New Small-Signal Parameter Extraction Technique for Large Gate-Periphery GaN HEMTs. IEEE Microwave and Wireless Components Letters, 2017, 27, 918-920.	2.0	22
8	Physics-Based Multi-Bias RF Large-Signal GaN HEMT Modeling and Parameter Extraction Flow. IEEE Journal of the Electron Devices Society, 2017, 5, 310-319.	1.2	59
9	Characterization and modeling of N-channel bulk FinFETs from DC to high frequency. , 2017, , .		3
10	GaN HEMT modeling for power and RF applications using ASM-HEMT. , 2016, , .		14
11	Modeling of source/drain access resistances and their temperature dependence in GaN HEMTs. , 2016, , .		36
12	Modeling of kink-effect in RF behaviour of GaN HEMTs using ASM-HEMT model. , 2016, , .		23
13	Capacitance Modeling in Dual Field-Plate Power GaN HEMT for Accurate Switching Behavior. IEEE Transactions on Electron Devices, 2016, 63, 565-572.	1.6	69
14	Modeling of trapping effects in GaN HEMTs. , 2015, , .		4
15	Effect of access region and field plate on capacitance behavior of GaN HEMT. , 2015, , .		10
16	Surface-Potential-Based Compact Modeling of Gate Current in AlGaIn/GaN HEMTs. IEEE Transactions on Electron Devices, 2015, 62, 443-448.	1.6	44
17	ASM-HEMT: Compact model for GaN HEMTs. , 2015, , .		24
18	A surface potential based model for GaN HEMTs. , 2013, , .		7

#	ARTICLE	IF	CITATIONS
19	Characterization of mutual heating inside a SiGe ring oscillator. , 2012, , .		4